

HIP4082

80V, 1.25A Peak Current H-Bridge FET Driver

FN3676
Rev.6.00
Feb 12, 2020

The HIP4082 is a medium frequency, medium voltage H-Bridge N-Channel MOSFET driver IC, available in 16 lead plastic SOIC (N) and DIP packages.

Specifically targeted for PWM motor control and UPS applications, bridge based designs are made simple and flexible with the HIP4082 H-bridge driver. With operation up to 80V, the device is best suited to applications of moderate power levels.

Similar to the HIP4081, it has a flexible input protocol for driving every possible switch combination except those which would cause a shoot-through condition. The HIP4082's reduced drive current allows smaller packaging and it has a much wider range of programmable dead times (0.1 to 4.5 μ s) making it ideal for switching frequencies up to 200kHz. The HIP4082 does not contain an internal charge pump, but does incorporate non-latching level-shift translation control of the upper drive circuits.

This set of features and specifications is optimized for applications where size and cost are important. For applications needing higher drive capability the HIP4080A and HIP4081A are recommended.

Features

- Independently Drives 4 N-Channel FET in Half Bridge or Full Bridge Configurations
- Bootstrap Supply Max Voltage to 95VDC
- Drives 1000pF Load in Free Air at 50°C with Rise and Fall Times of Typically 15ns
- User-Programmable Dead Time (0.1 to 4.5 μ s)
- DIS (Disable) Overrides Input Control and Refreshes Bootstrap Capacitor when Pulled Low
- Input Logic Thresholds Compatible with 5V to 15V Logic Levels
- Shoot-Through Protection
- Undervoltage Protection
- Pb-Free Plus Anneal Available (RoHS Compliant)

Applications

- UPS Systems
- DC Motor Controls
- Full Bridge Power Supplies
- Switching Power Amplifiers
- Noise Cancellation Systems
- Battery Powered Vehicles
- Peripherals
- Medium/Large Voice Coil Motors
- Related Literature
 - TB363, Guidelines for Handling and Processing Moisture Sensitive Surface Mount Devices (SMDs)

Ordering Information

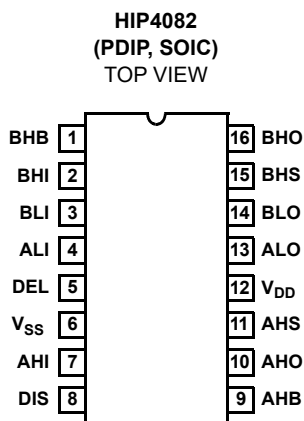
PART NUMBER	PART MARKING	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
HIP4082IBZ* (Note)	4082IBZ	-55 to +125	16 Ld SOIC (N) (Pb-free)	M16.15
HIP4082IPZ (Note)	HIP4082IPZ	-55 to +125	16 Ld PDIP** (Pb-free)	E16.3

*Add "T" suffix for tape and reel.

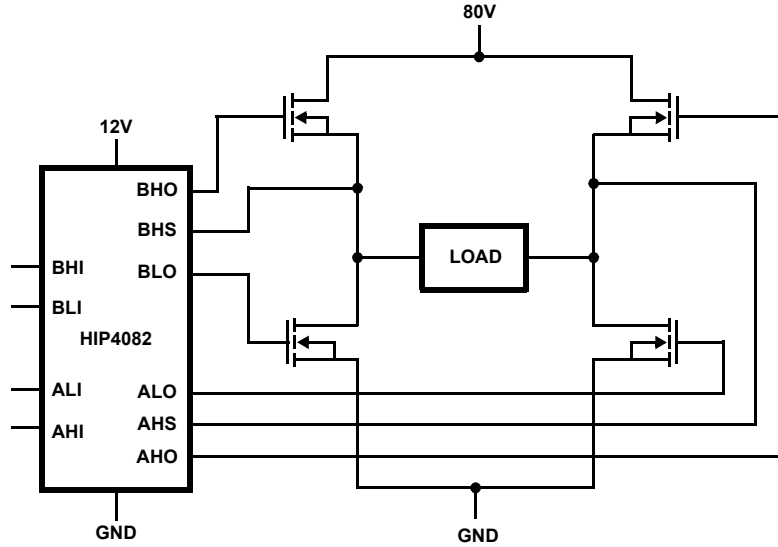
NOTE: Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

**Pb-free PDIPs can be used for through hole wave solder processing only. They are not intended for use in Reflow solder processing applications.

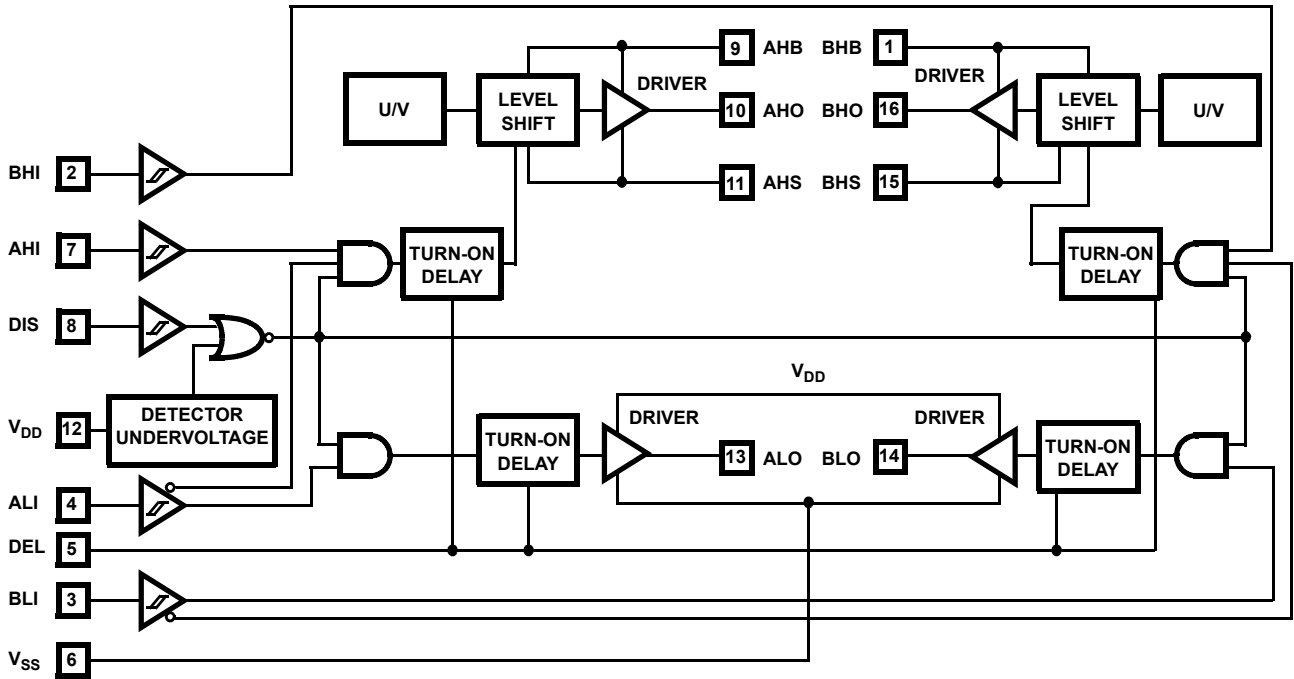
Pinout



Application Block Diagram



Functional Block Diagram



Absolute Maximum Ratings

Supply Voltage, V_{DD} -0.3V to 16V
 Logic I/O Voltages -0.3V to $V_{DD} + 0.3V$
 Voltage on AHS, BHS -6V (Transient) to 80V (25°C to 150°C)
 Voltage on AHS, BHS -6V (Transient) to 70V (-55°C to 150°C)
 Voltage on AHB, BHB $V_{AHS, BHS} - 0.3V$ to $V_{AHS, BHS} + V_{DD}$
 Voltage on ALO, BLO $V_{SS} - 0.3V$ to $V_{DD} + 0.3V$
 Voltage on AHO, BHO $V_{AHS, BHS} - 0.3V$ to $V_{AHB, BHB} + 0.3V$ Input
 Current, DEL -5mA to 0mA
 Phase Slew Rate 20V/ns
 NOTE: All voltages are relative V_{SS} unless otherwise specified.

Thermal Information

Thermal Resistance θ_{JA} (°C/W)
 SOIC Package 115
 DIP Package 90
 Maximum Power Dissipation See Curve
 Storage Temperature Range -65°C to +150°C
 Operating Max. Junction Temperature +150°C
 Lead Temperature (Soldering 10s) +300°C
 (For SOIC - Lead Tips Only)

Operating Conditions

Supply Voltage, V_{DD} +8.5V to +15V
 Voltage on V_{SS} -1.0V to +1.0V
 Voltage on AHB, BHB $V_{AHS, BHS} + 7.5V$ to $V_{AHS, BHS} + V_{DD}$
 Input Current, DEL -4mA to -100µA

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Specifications $V_{DD} = V_{AHB} = V_{BHB} = 12V, V_{SS} = V_{AHS} = V_{BHS} = 0V, R_{DEL} = 100K$

PARAMETER	SYMBOL	TEST CONDITIONS	$T_J = +25^\circ C$			$T_J = -55^\circ C$ TO $+150^\circ C$		UNITS
			MIN	TYP	MAX	MIN	MAX	
SUPPLY CURRENTS & UNDER VOLTAGE PROTECTION								
V_{DD} Quiescent Current	I_{DD}	All inputs = 0V, $R_{DEL} = 100K$	1.2	2.3	3.5	0.85	4	mA
		All inputs = 0V, $R_{DEL} = 10K$	2.2	4.0	5.5	1.9	6.0	mA
V_{DD} Operating Current	I_{DDO}	f = 50kHz, no load	1.5	2.6	4.0	1.1	4.2	mA
		50kHz, no load, $R_{DEL} = 10k\Omega$	2.5	4.0	6.4	2.1	6.6	mA
AHB, BHB Off Quiescent Current	I_{AHBL}, I_{BHBL}	AHI = BHI = 0V	0.5	1.0	1.5	0.4	1.6	mA
AHB, BHB On Quiescent Current	I_{AHBH}, I_{BHBH}	AHI = BHI = V_{DD}	65	145	240	40	250	µA
AHB, BHB Operating Current	I_{AHBO}, I_{BHBO}	f = 50kHz, CL = 1000pF	.65	1.1	1.8	.45	2.0	mA
AHS, BHS Leakage Current	I_{HLK}	$V_{AHS} = V_{BHS} = 80V$ $V_{AHB} = V_{BHB} = 96$ $V_{DD} =$ Not Connected	-	-	1.0	-	-	µA
V_{DD} Rising Undervoltage Threshold	V_{DDUV+}		6.8	7.6	8.25	6.5	8.5	V
V_{DD} Falling Undervoltage Threshold	V_{DDUV-}		6.5	7.1	7.8	6.25	8.1	V
Undervoltage Hysteresis	UVHYS		0.17	0.4	0.75	0.15	0.90	V
AHB, BHB Undervoltage Threshold	VHBUV	Referenced to AHS & BHS	5	6.0	7	4.5	7.5	V
INPUT PINS: ALI, BLI, AHI, BHI, & DIS								
Low Level Input Voltage	V_{IL}	Full Operating Conditions	-	-	1.0	-	0.8	V
High Level Input Voltage	V_{IH}	Full Operating Conditions	2.5	-	-	2.7	-	V
Input Voltage Hysteresis			-	35	-	-	-	mV
Low Level Input Current	I_{IL}	$V_{IN} = 0V$, Full Operating Conditions	-145	-100	-60	-150	-50	µA
High Level Input Current	I_{IH}	$V_{IN} = 5V$, Full Operating Conditions	-1	-	+1	-10	+10	µA
TURN-ON DELAY PIN DEL								
Dead Time	T_{DEAD}	$R_{DEL} = 100K$	2.5	4.5	8.0	2.0	8.5	µs
		$R_{DEL} = 10K$	0.27	0.5	0.75	0.2	0.85	µs

Electrical Specifications $V_{DD} = V_{AHB} = V_{BHB} = 12V, V_{SS} = V_{AHS} = V_{BHS} = 0V, R_{DEL} = 100K$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	$T_J = +25^\circ C$			$T_J = -55^\circ C$ TO $+150^\circ C$		UNITS
			MIN	TYP	MAX	MIN	MAX	
GATE DRIVER OUTPUT PINS: ALO, BLO, AHO, & BHO								
Low Level Output Voltage	V_{OL}	$I_{OUT} = 50mA$	0.65		1.1	0.5	1.2	V
High Level Output Voltage	$V_{DD}-V_{OH}$	$I_{OUT} = -50mA$	0.7		1.2	0.5	1.3	V
Peak Pullup Current	I_{O+}	$V_{OUT} = 0V$	1.1	1.4	2.5	0.85	2.75	A
Peak Pulldown Current	I_{O-}	$V_{OUT} = 12V$	1.0	1.3	2.3	0.75	2.5	A

Switching Specifications $V_{DD} = V_{AHB} = V_{BHB} = 12V, V_{SS} = V_{AHS} = V_{BHS} = 0V, R_{DEL} = 100K, C_L = 1000pF$.

PARAMETER	SYMBOL	TEST CONDITIONS	$T_J = +25^\circ C$			$T_J = -55^\circ C$ TO $+150^\circ C$		UNITS
			MIN	TYP	MAX	MIN	MAX	
Lower Turn-off Propagation Delay (ALI-ALO, BLI-BLO)	T_{LPHL}		-	25	50	-	70	ns
Upper Turn-off Propagation Delay (AHI-AHO, BHI-BHO)	T_{HPHL}		-	55	80	-	100	ns
Lower Turn-on Propagation Delay (ALI-ALO, BLI-BLO)	T_{LPLH}		-	40	85	-	100	ns
Upper Turn-on Propagation Delay (AHI-AHO, BHI-BHO)	T_{HPLH}		-	75	110	-	150	ns
Rise Time	T_R		-	9	20	-	25	ns
Fall Time	T_F		-	9	20	-	25	ns
Minimum Input Pulse Width	$T_{PWIN-ON/OFF}$		50	-	-	50	-	ns
Output Pulse Response to 50 ns Input Pulse	T_{PWOUT}			63			80	ns
Disable Turn-off Propagation Delay (DIS - Lower Outputs)	T_{DISLOW}		-	50	80	-	90	ns
Disable Turn-off Propagation Delay (DIS - Upper Outputs)	$T_{DISHIGH}$		-	75	100	-	125	ns
Disable Turn-on Propagation Delay (DIS - ALO & BLO)	T_{DLPLH}		-	40	70	-	100	ns
Disable Turn-on Propagation Delay (DIS- AHO & BHO)	T_{DHPLH}	$R_{DEL} = 10K$	-	1.2	2	-	3	μs
Refresh Pulse Width (ALO & BLO)	T_{REF-PW}		375	580	900	350	950	ns

TRUTH TABLE

INPUT					OUTPUT	
ALI, BLI	AHI, BHI	VDDUV	VHBUV	DIS	ALO, BLO	AHO, BHO
X	X	X	X	1	0	0
X	X	1	X	X	0	0
0	X	0	1	0	0	0
1	X	0	X	0	1	0
0	1	0	0	0	0	1
0	0	0	0	0	0	0

NOTE: X signifies that input can be either a "1" or "0".

Pin Descriptions

PIN NUMBER	SYMBOL	DESCRIPTION
1	BHB	B High-side Bootstrap supply. External bootstrap diode and capacitor are required. Connect cathode of bootstrap diode and positive side of bootstrap capacitor to this pin.
2	BHI	B High-side Input. Logic level input that controls BHO driver (Pin 16). BLI (Pin 3) high level input overrides BHI high level input to prevent half-bridge shoot-through, see Truth Table. DIS (Pin 8) high level input overrides BHI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}).
3	BLI	B Low-side Input. Logic level input that controls BLO driver (Pin 14). If BHI (Pin 2) is driven high or not connected externally then BLI controls both BLO and BHO drivers, with dead time set by delay currents at DEL (Pin 5). DIS (Pin 8) high level input overrides BLI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}).
4	ALI	A Low-side Input. Logic level input that controls ALO driver (Pin 13). If AHI (Pin 7) is driven high or not connected externally then ALI controls both ALO and AHO drivers, with dead time set by delay currents at DEL (Pin 5). DIS (Pin 8) high level input overrides ALI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}).
5	DEL	Turn-on DELay. Connect resistor from this pin to V_{SS} to set timing current that defines the dead time between drivers. All drivers turn-off with no adjustable delay, so the DEL resistor guarantees no shoot-through by delaying the turn-on of all drivers. The voltage across the DEL resistor is approximately $V_{DD} - 2V$.
6	V_{SS}	Chip negative supply, generally will be ground.
7	AHI	A High-side Input. Logic level input that controls AHO driver (Pin 10). ALI (Pin 4) high level input overrides AHI high level input to prevent half-bridge shoot-through, see Truth Table. DIS (Pin 8) high level input overrides AHI high level input. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}).
8	DIS	DISable input. Logic level input that when taken high sets all four outputs low. DIS high overrides all other inputs. When DIS is taken low the outputs are controlled by the other inputs. The pin can be driven by signal levels of 0V to 15V (no greater than V_{DD}).
9	AHB	A High-side Bootstrap supply. External bootstrap diode and capacitor are required. Connect cathode of bootstrap diode and positive side of bootstrap capacitor to this pin.
10	AHO	A High-side Output. Connect to gate of A High-side power MOSFET.
11	AHS	A High-side Source connection. Connect to source of A High-side power MOSFET. Connect negative side of bootstrap capacitor to this pin.
12	V_{DD}	Positive supply to control logic and lower gate drivers. De-couple this pin to V_{SS} (Pin 6).
13	ALO	A Low-side Output. Connect to gate of A Low-side power MOSFET.
14	BLO	B Low-side Output. Connect to gate of B Low-side power MOSFET.
15	BHS	B High-side Source connection. Connect to source of B High-side power MOSFET. Connect negative side of bootstrap capacitor to this pin.
16	BHO	B High-side Output. Connect to gate of B High-side power MOSFET.

Timing Diagrams

X = A OR B, A AND B HALVES OF BRIDGE CONTROLLER ARE INDEPENDENT

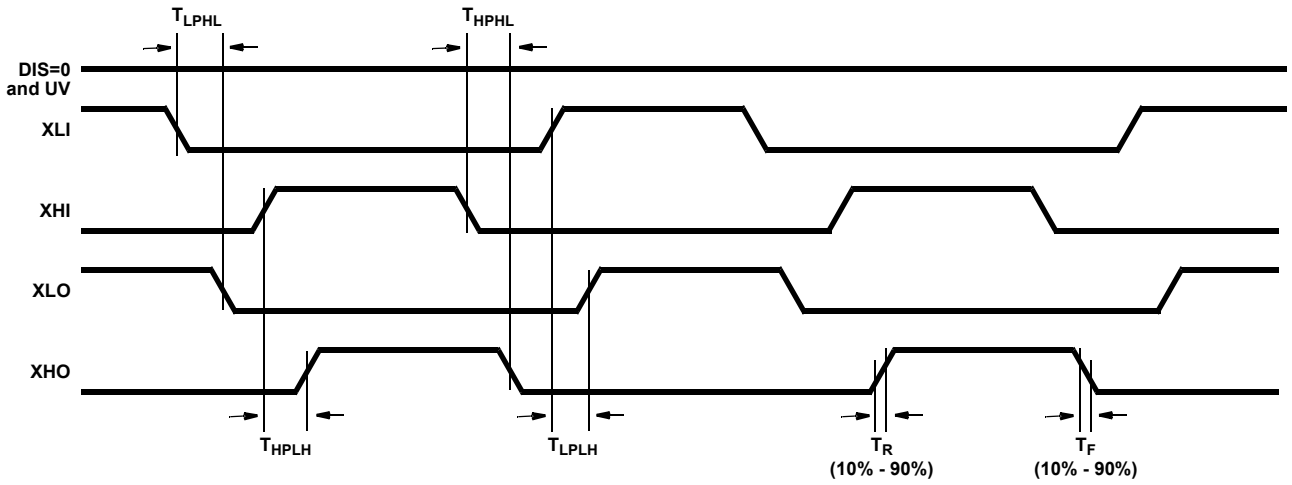


FIGURE 1. INDEPENDENT MODE

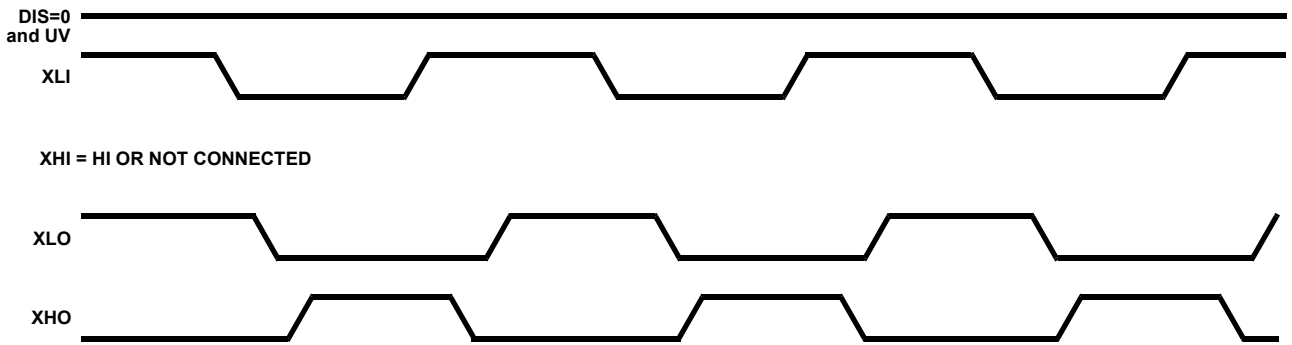


FIGURE 2. BISTATE MODE

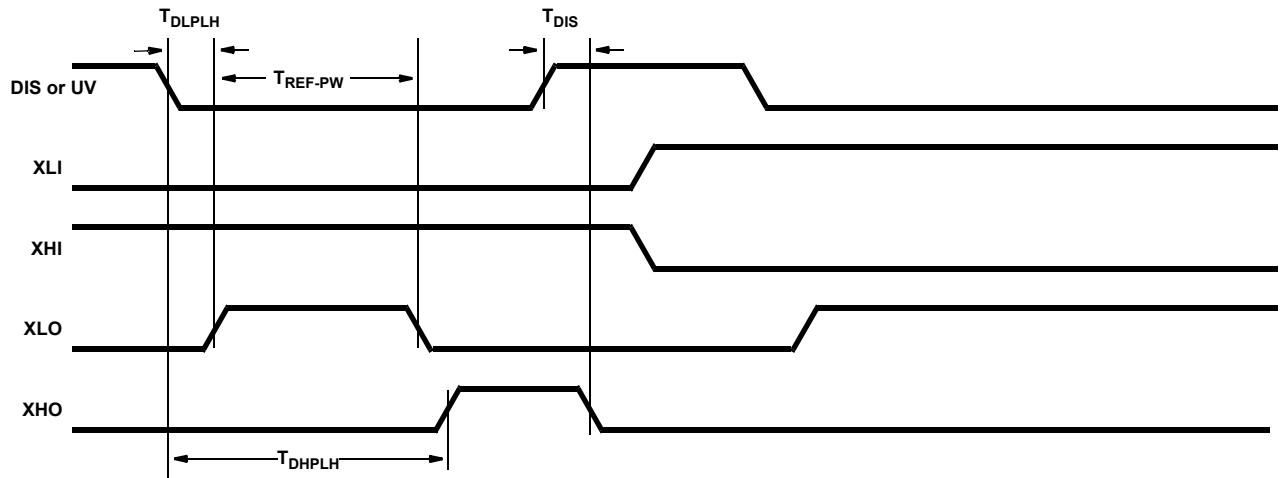


FIGURE 3. DISABLE FUNCTION

Performance Curves

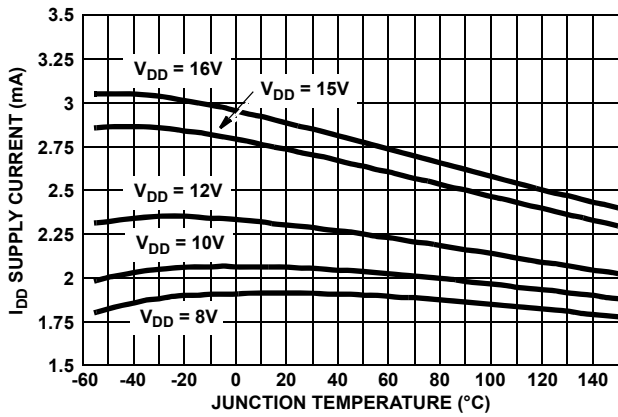


FIGURE 4. I_{DD} SUPPLY CURRENT vs TEMPERATURE AND V_{DD} SUPPLY VOLTAGE

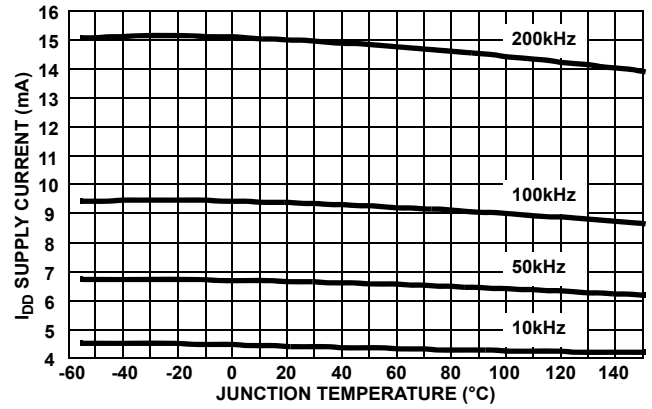


FIGURE 5. V_{DD} SUPPLY CURRENT vs TEMPERATURE AND SWITCHING FREQUENCY (1000pF LOAD)

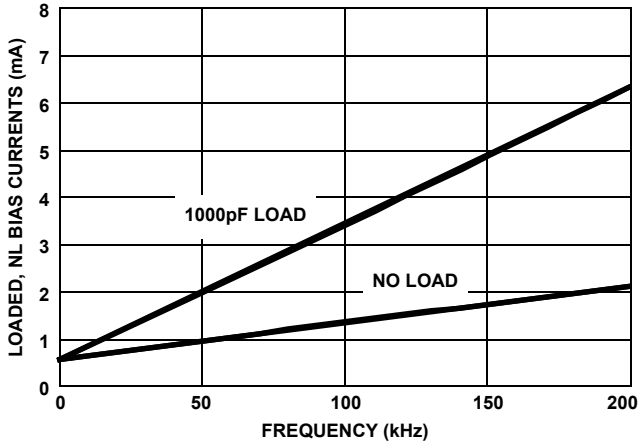


FIGURE 6. FLOATING (IXHB) BIAS CURRENT vs FREQUENCY AND LOAD

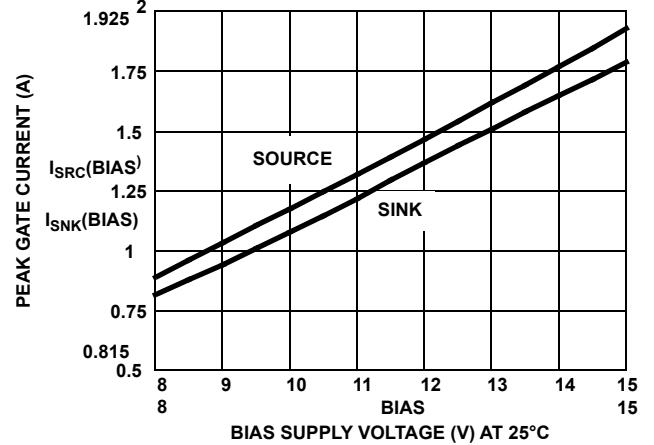


FIGURE 7. GATE SOURCE/SINK PEAK CURRENT vs BIAS SUPPLY VOLTAGE AT 25°C

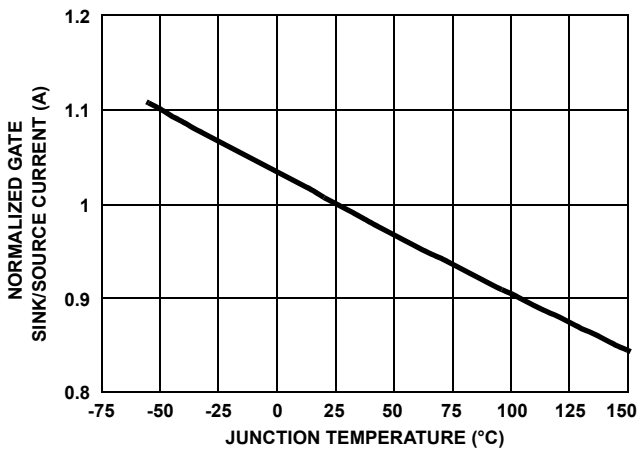


FIGURE 8. GATE CURRENT vs TEMPERATURE, NORMALIZED TO 25°C

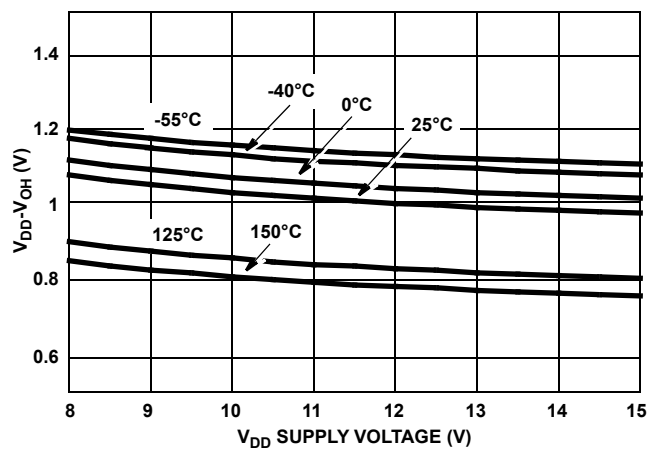


FIGURE 9. $V_{DD}-V_{OH}$ vs BIAS VOLTAGE TEMPERATURE

Performance Curves (Continued)

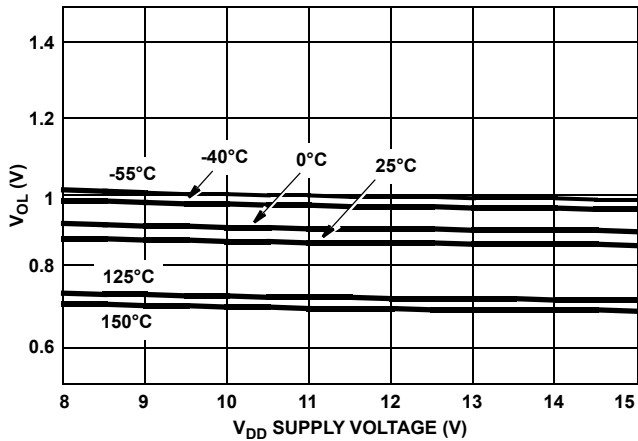


FIGURE 10. V_{OL} vs BIAS VOLTAGE AND TEMPERATURE

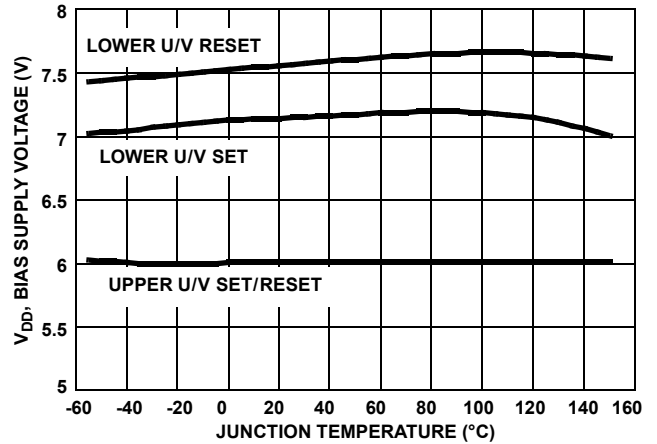


FIGURE 11. UNDERVOLTAGE TRIP VOLTAGES vs TEMPERATURE

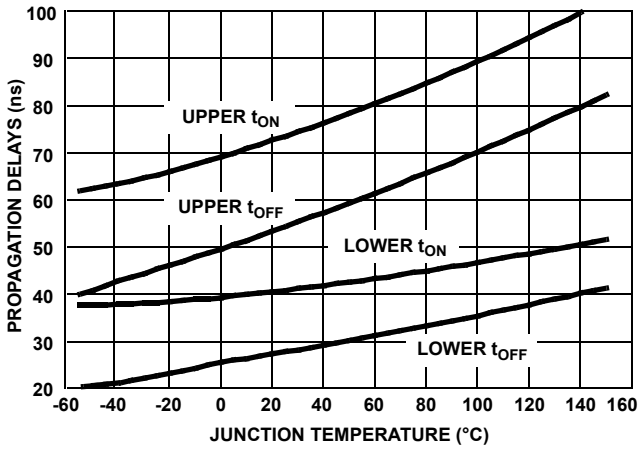


FIGURE 12. UPPER LOWER TURN-ON/TURN-OFF PROPAGATION DELAY vs TEMPERATURE

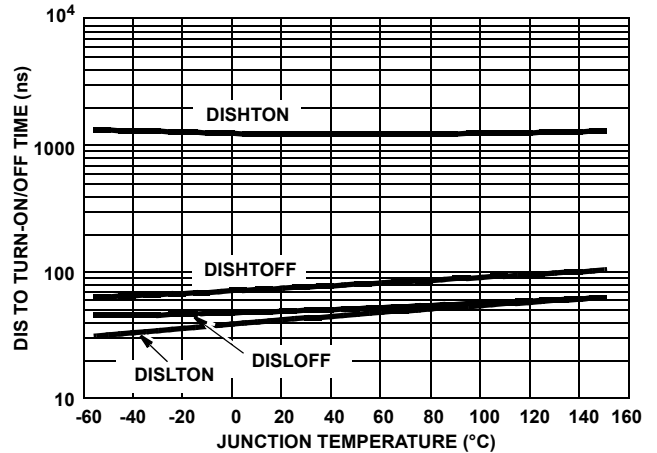


FIGURE 13. UPPER/LOWER DIS(ABLE) TO TURN-ON/OFF vs TEMPERATURE (°C)

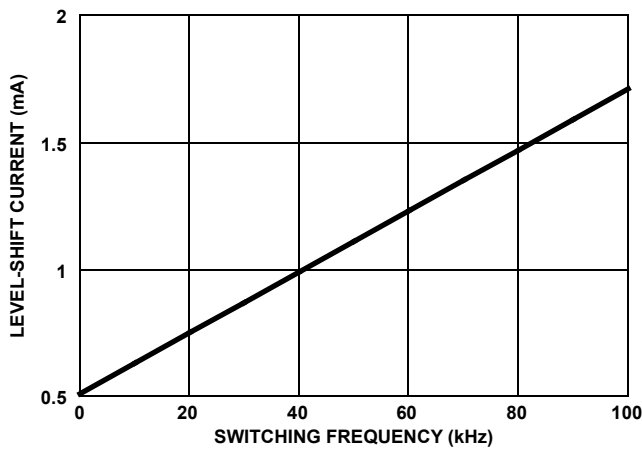


FIGURE 14. FULL BRIDGE LEVEL-SHIFT CURRENT vs FREQUENCY (kHz)

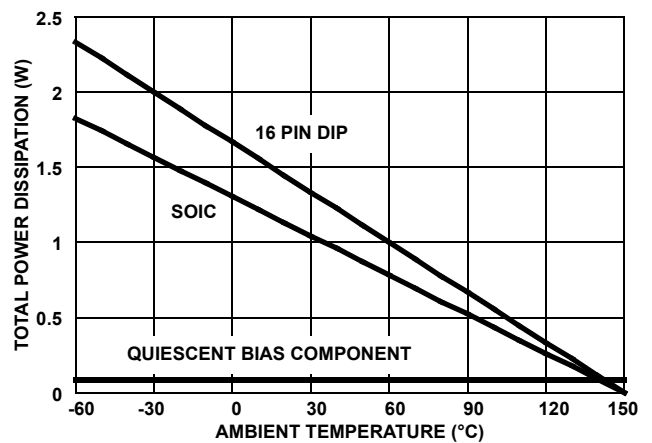


FIGURE 15. MAXIMUM POWER DISSIPATION vs AMBIENT TEMPERATURE

Performance Curves (Continued)

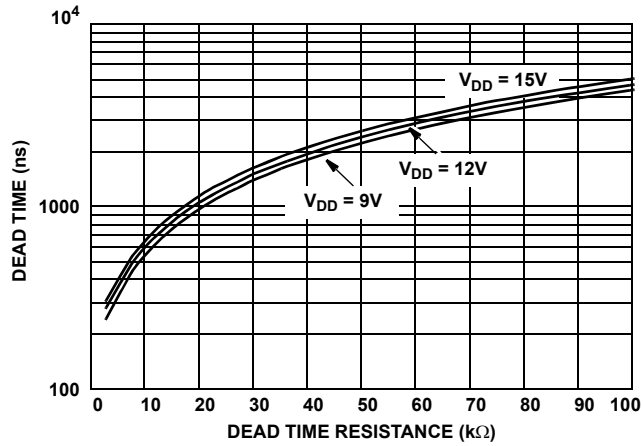


FIGURE 16. DEAD-TIME vs DEL RESISTANCE AND BIAS SUPPLY (V_{DD}) VOLTAGE

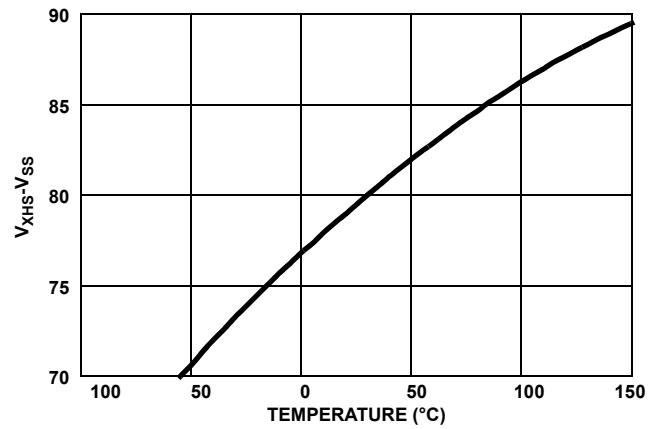


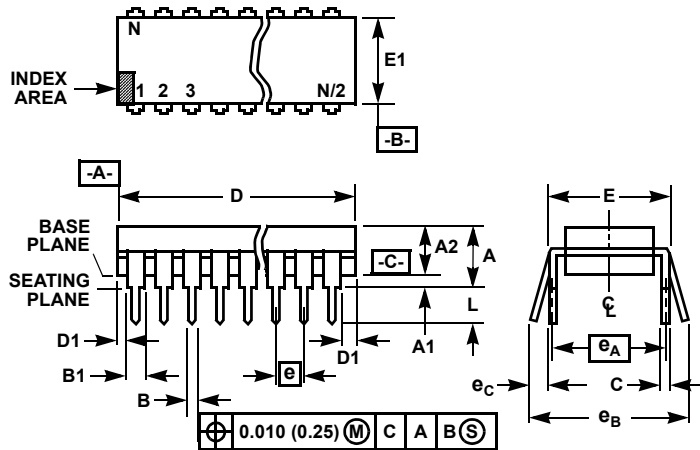
FIGURE 17. MAXIMUM OPERATING PEAK AHS/BHS VOLTAGE vs TEMPERATURE

Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to the web to make sure that you have the latest revision.

DATE	REVISION	CHANGE
Feb 12, 2020	FN3676.6	Updated Ordering information table on page 2. Removed About Intersil section. Updated POD M16.15 to the latest revision, changes are as follows: -Updated graphics to new standard layout, removing the dimension table. Updated disclaimer.
Sep 30, 2015	FN3676.5	Updated the Ordering Information Table on page 2. Added Revision History and About Intersil sections.

Package Outline Drawings



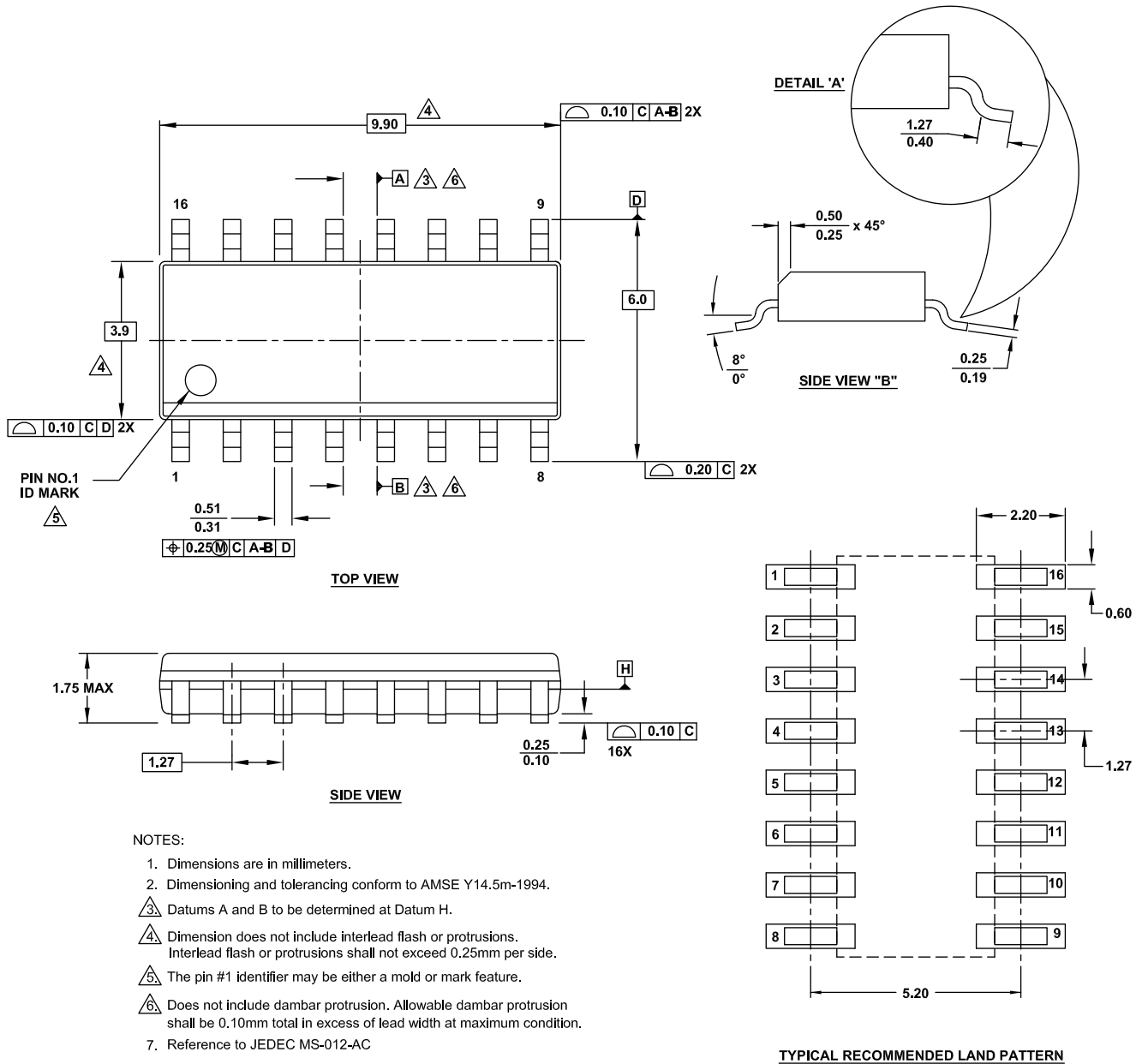
NOTES:

- Controlling Dimensions: INCH. In case of conflict between English and Metric dimensions, the inch dimensions control.
- Dimensioning and tolerancing per ANSI Y14.5M-1982.
- Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication No. 95.
- Dimensions A, A1 and L are measured with the package seated in JEDEC seating plane gauge GS-3.
- D, D1, and E1 dimensions do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010 inch (0.25mm).
- E and e_A are measured with the leads constrained to be perpendicular to datum $-C-$.
- e_B and e_C are measured at the lead tips with the leads unconstrained. e_C must be zero or greater.
- B1 maximum dimensions do not include dambar protrusions. Dambar protrusions shall not exceed 0.010 inch (0.25mm).
- N is the maximum number of terminal positions.
- Corner leads (1, N, N/2 and N/2 + 1) for E8.3, E16.3, E18.3, E28.3, E42.6 will have a B1 dimension of 0.030 - 0.045 inch (0.76 - 1.14mm).

**E16.3 (JEDEC MS-001-BB ISSUE D)
16 LEAD DUAL-IN-LINE PLASTIC PACKAGE (PDIP)**

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	-	0.210	-	5.33	4
A1	0.015	-	0.39	-	4
A2	0.115	0.195	2.93	4.95	-
B	0.014	0.022	0.356	0.558	-
B1	0.045	0.070	1.15	1.77	8, 10
C	0.008	0.014	0.204	0.355	-
D	0.735	0.775	18.66	19.68	5
D1	0.005	-	0.13	-	5
E	0.300	0.325	7.62	8.25	6
E1	0.240	0.280	6.10	7.11	5
e	0.100 BSC		2.54 BSC		-
e_A	0.300 BSC		7.62 BSC		6
e_B	-	0.430	-	10.92	7
L	0.115	0.150	2.93	3.81	4
N	16		16		9

Rev. 0 12/93



Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
 2. Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
 3. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
 4. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
 5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.
 - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.
 - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user's manual or other Renesas Electronics document.
 6. When using Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
 7. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
 8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
 9. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
 10. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
 11. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
 12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.
- (Note1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.
- (Note2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.4.0-1 November 2017)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,
Koto-ku, Tokyo 135-0061, Japan
www.renesas.com

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit:
www.renesas.com/contact/

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.